



IBM Technology Development

Thinking in 3D, Improving performance and modularity

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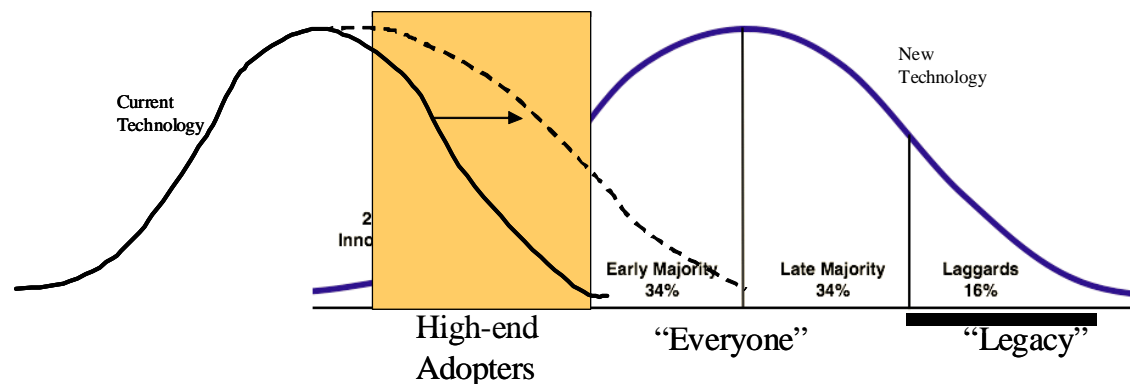
FDIP 2010

3D/TSV

- What is it? Why do we think it is interesting?
- Broader system level thought process required
- Thinking/executing in 3 dimensions
- Some Challenges for us

- Although there is a fair amount of industry activity working to bring 3D (actually the via) to fruition... what is new about 3D anyway?
 - Concept of 3D not really new... wire-bonding, PAM, PoP, etc.
 - Via structure, size, shape, Lithography, and material improvements
 - EDA enablement / improvements (floor planning, timing, simulation, verification, test)
 - Interest in continuing along Moores' law course

- Wow factor needed, coupled with 2D thinking challenges 3D/TSV technology introduction.
 - A compelling reason to invest and take the risk is needed (ultimately no other way)
 - *There is a difference between designing for 3D, and designing with 2D back-up.*
 - **Challenges, values, general inertia of applying a new technology.**
 - Limitations and considerations of power distribution, thermal, etc.
 - Necessitates a more comprehensive, system floor planning methodology



- ▶ So, In general, what is it ?
 - At it's base, a hole thru the semiconductor enabling connections on both sides of flip-chip devices
 - Some what different definition/process depending on your perspective and role within the industry
- ▶ Why is it interesting to the industry?
 - Tracking Moore's law, Integration, Performance, Cost, ...
- ▶ What are the considerations to using this technology?
 - General shape and performance value or impact of this via capability
 - Typical new, risk / reward equations still apply
 - Application/system level view vs. floor planning impacts
 - Tools (EDA and Fab), Integration, definition, process

■ **Performance**

- Shorter nets,
- Lower capacitance interconnect

■ **Size / Density**

- Moore's law
- Smaller I/O blocks
- Tighter integration
- Less mass

■ **Reduced power**

- Lower capacitance and shorter nets
- Less re-power across chip
- Less complex chip-chip I/O

■ **Modularity/Reuse**

- Mixing technologies
- Cost

The “base”, path between two Single chip packages

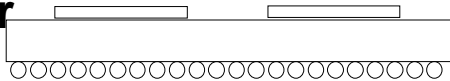


Signal Path: Driver-Last Metal, ball, ~15mm package, BGA, 50mm card, BGA, ~15mm package, ball, Last Metal-Receiver

Traditional ESD devices required, driver and receiver often complex (pre-compensation, DFE, etc.)

Bus-width limited typically by package I/O count, Frequency typically limited by channel attenuation

A MCM/SiP Chip to Chip path on same carrier

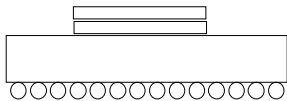


Signal Path: Driver-Last Metal, ball, ~15mm package, ball, Last Metal-Receiver

Traditional ESD devices usually still required, drivers and receivers typically less complex

Bus-width limited typically by chip I/O and ability to escape into and thru the package. Frequency less limited by channel

Stacked Devices, Chip to Chip Vertically



Signal Path: Driver-chip wire, TSV, chip wire-Receiver

ESD may be reduced, driver and receiver potentially much less complex

Bus-width limited only by TSV pitch/count (compared to the “base” above, virtually unlimited), bus frequency limited by circuits and impacts of thermal, noise, power distribution driven density.

- **Management of typically more items simultaneously**
 - ▶ Floor planning much more complex
 - ▶ Complexity more like system / product level than traditional 2D
 - Layer to layer interactions
 - Each layer to outside world

- **Utilization of 3D**
 - ▶ **Mixing technologies**
 - High value potential
 - ▶ Layer-layer interaction
 - ▶ Memory / Processor integration
 - ▶ **Reusing IP**
 - TSV impacts
 - Stacking multiples of the same layer
 - ▶ **Signaling**
 - Layer to layer, vs. off-stack or off-module
 - Driver selection / flexibility
 - Which layer do we drive off-stack or off-module from
 - ▶ **Pre-planning/standardizing interconnects**

- **Basics**

- ▶ Thermal interaction layer-layer and at the module level
 - Hot spots
 - Where should the high power layer go?
- ▶ Electrical
 - Planning for voltage requirements, now and future
 - Timing, clocking,
- ▶ Structure and stack effect on electro-migration, current limitations...

- **Other**

- ▶ Test
- ▶ Debug
- ▶ Etc.

- **Organizational effects**

- ▶ Module/System integration visibility

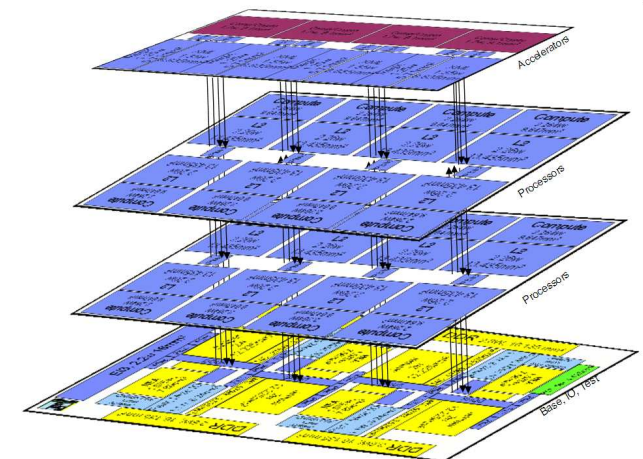
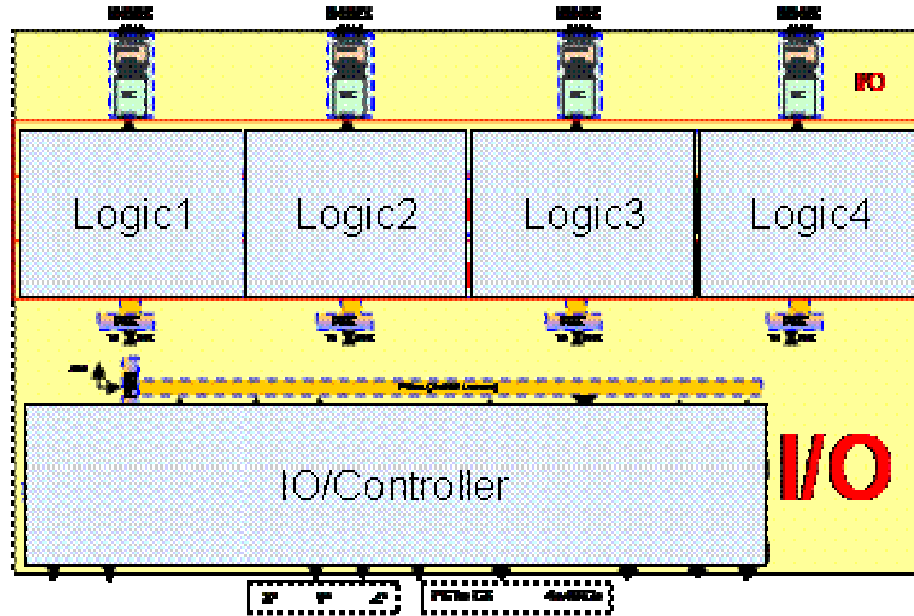
An example thought flow

Structure / stacking etc.

Baseline - How to extend a the range of a current product

Extending design / increasing modularity/reuse

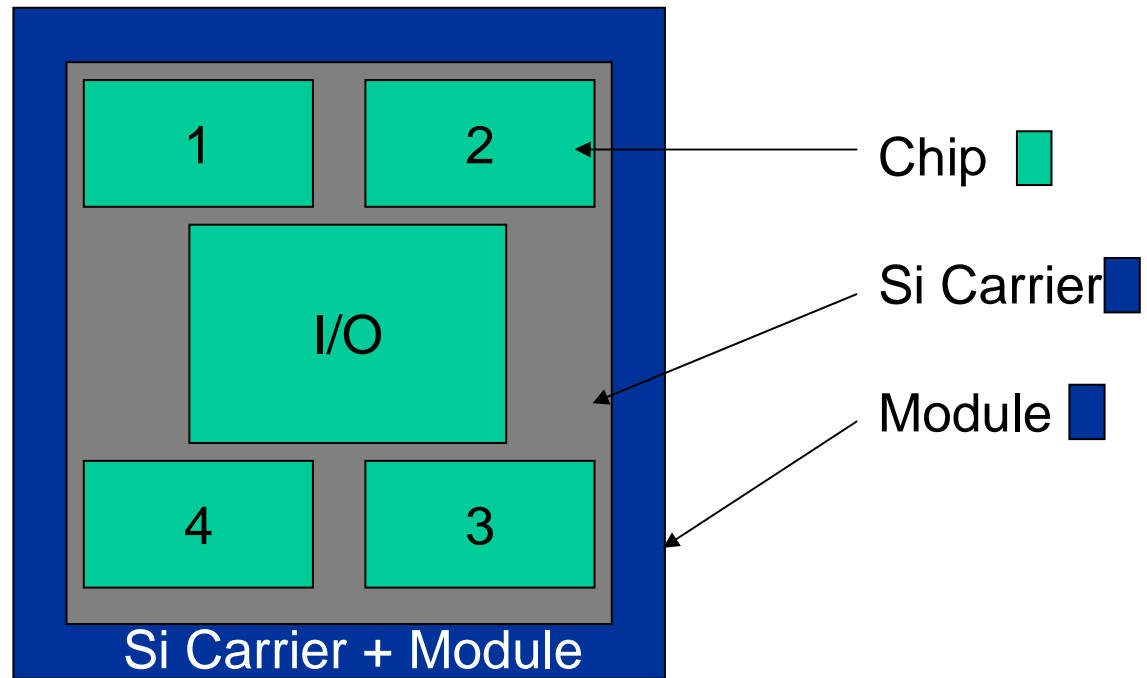
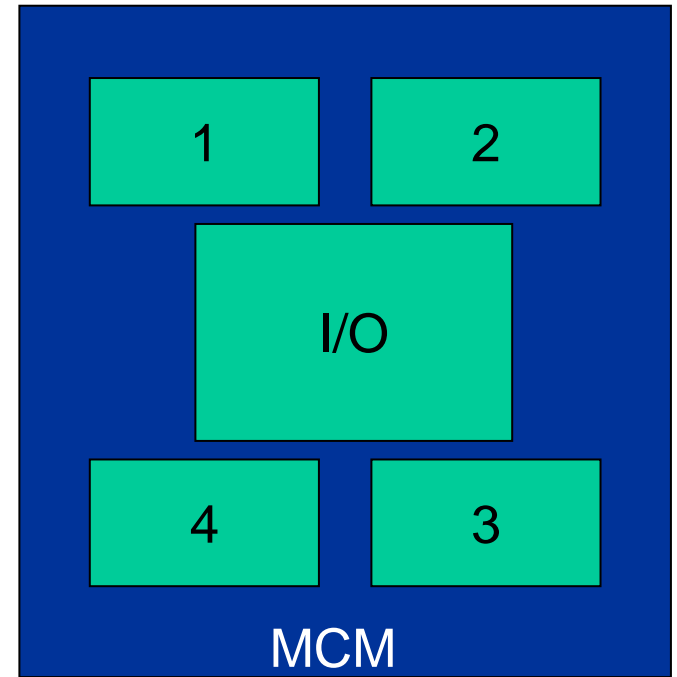
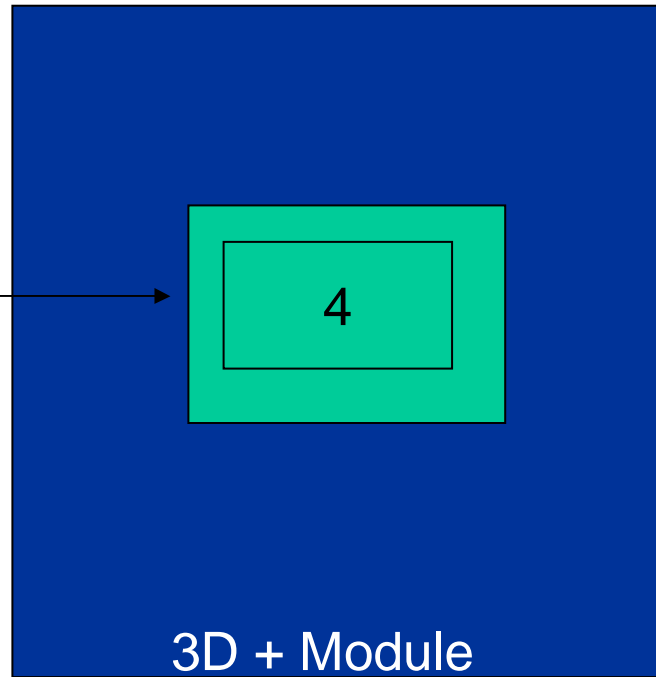
► Creating a 4X capable product extension



Essentially repeat 4 times the function of the original product

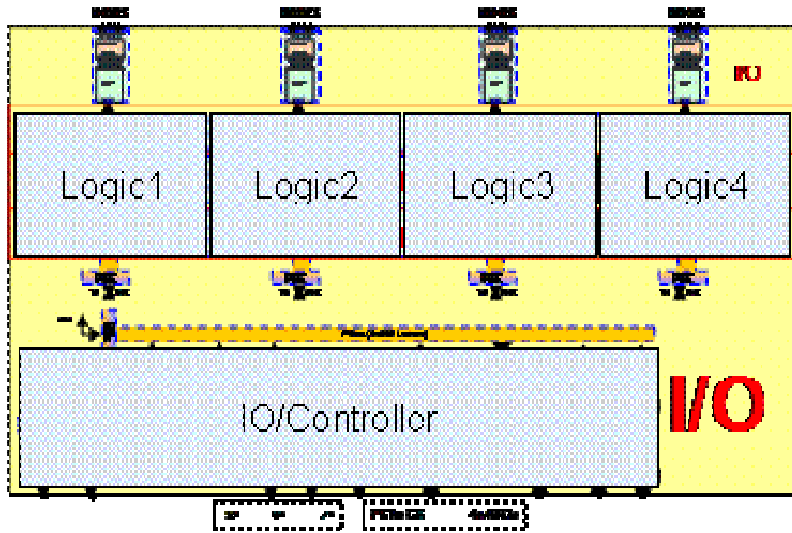
- Performance of Internal interconnect bus increased by changing the direction of the flow. I/O bandwidth value exploited

Packaging Options

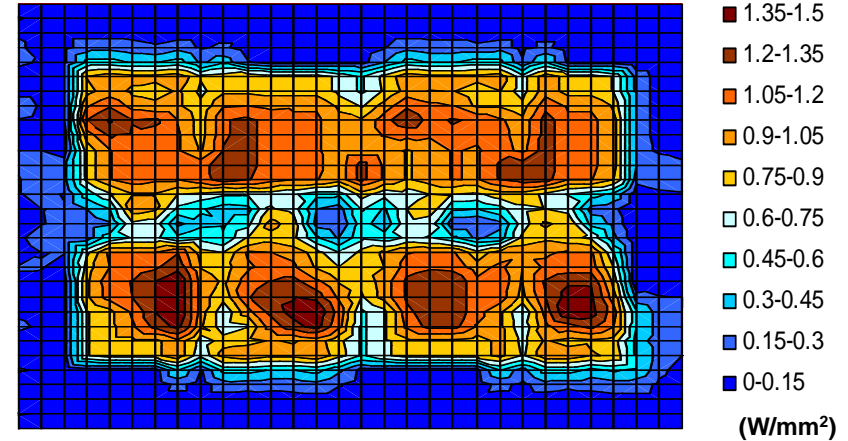


Extending design / increasing modularity/reuse

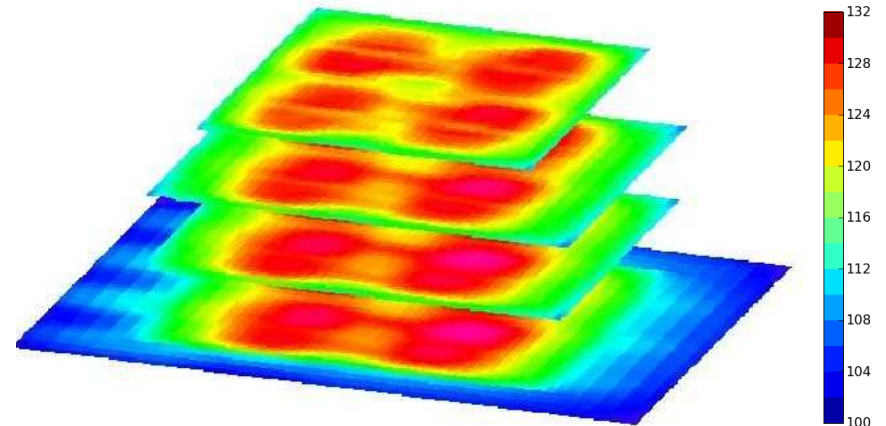
► Proposed 3D Configuration



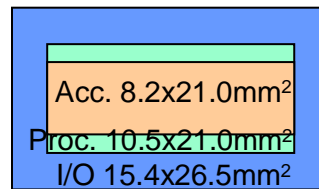
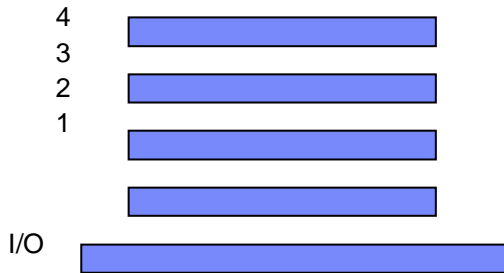
Aggregated power density



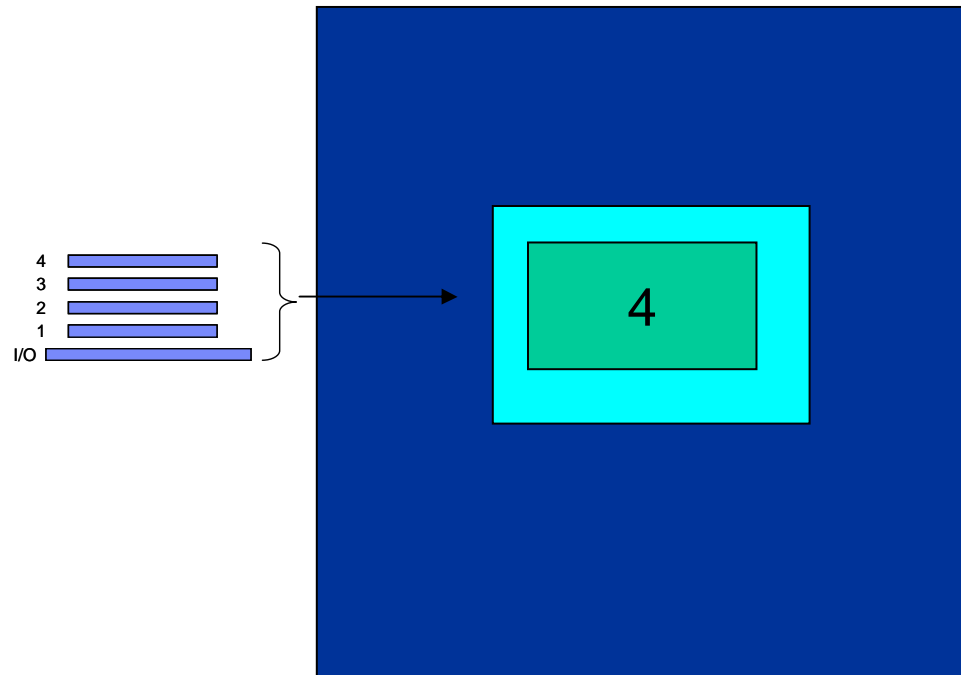
3D Thermal Map



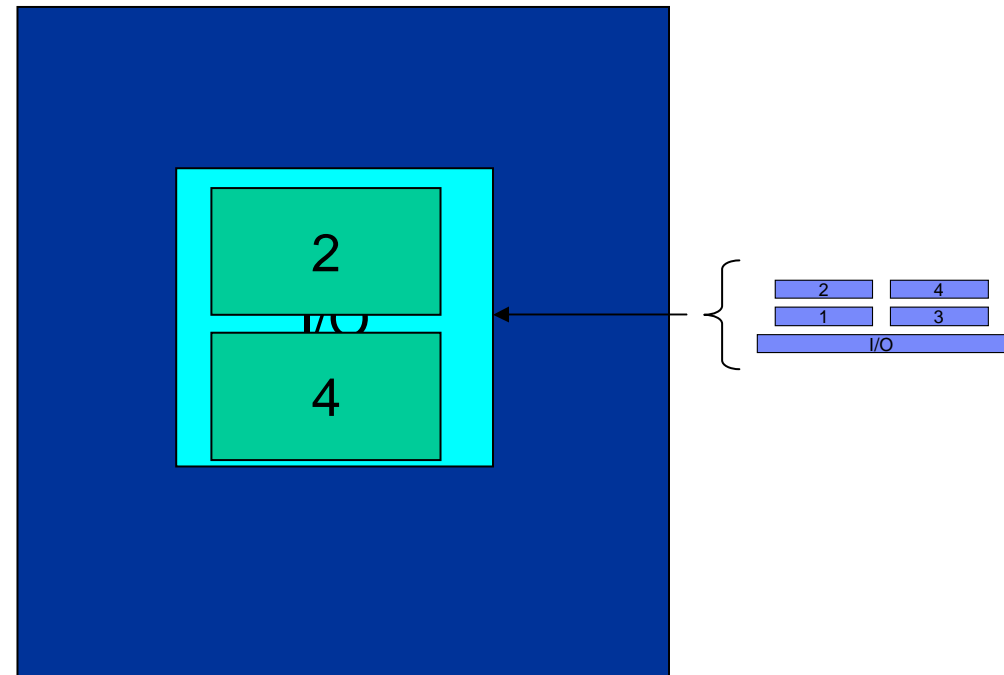
Top view



Alternative 3D Stack Sequence



5 High Stack

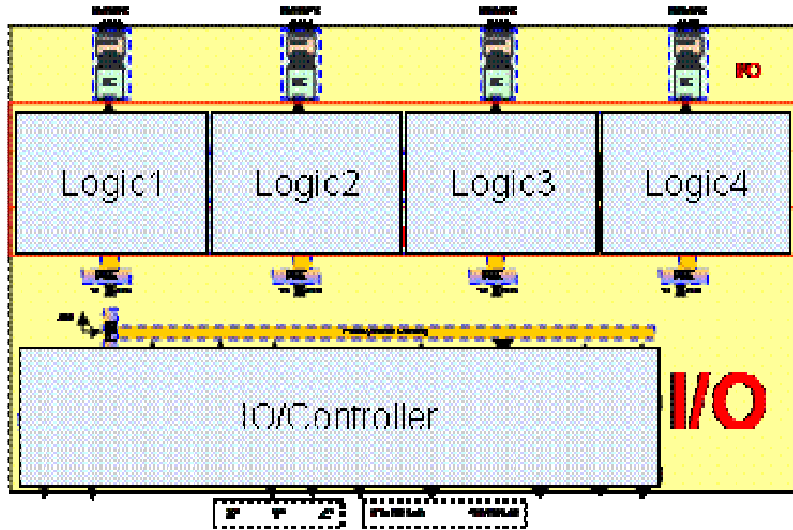


"Paired" 3 High Stack

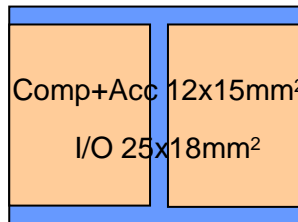
- add 2x2.5mm wings to I/O layer
 - ▶ - 14.5x21mm => 19.5x21mm
 - ▶ - ~100mm² area adder
- change aspect ratio of I/O layer + wings
 - ▶ - 14.5x21mm => 17.5x17.5mm
 - ▶ - still need to add ~ 50-65mm²

Extending design / increasing modularity/reuse

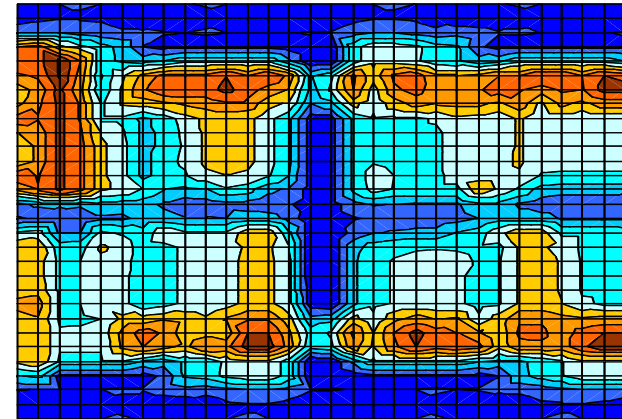
► Proposed 3D Configuration



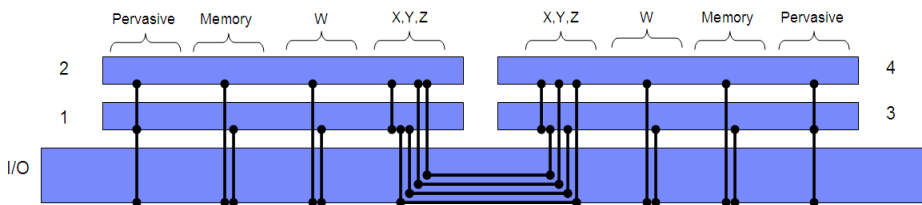
Top view



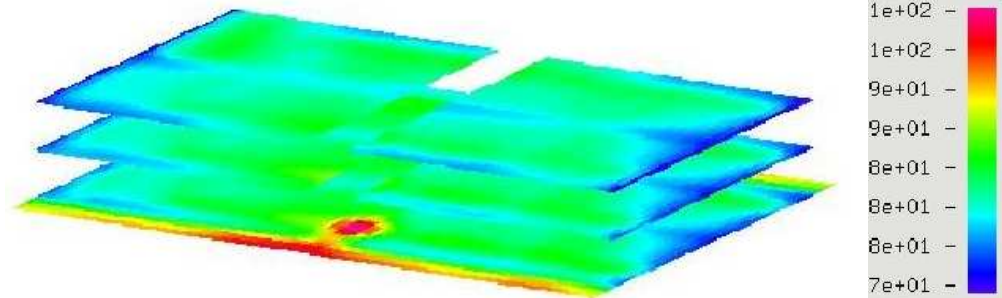
Aggregated power density



- 0.9-1
 - 0.8-0.9
 - 0.7-0.8
 - 0.6-0.7
 - 0.5-0.6
 - 0.4-0.5
 - 0.3-0.4
 - 0.2-0.3
 - 0.1-0.2
 - 0-0.1
- (W/mm²)



3D Thermal Map



Challenge for us

- 3D technology optimization requires 3D thinking, and system level thought processes.
- Floor-planning tools/methodology must continue to evolve as the potential capability enabled by 3D/TSV drives increasing complexity.